

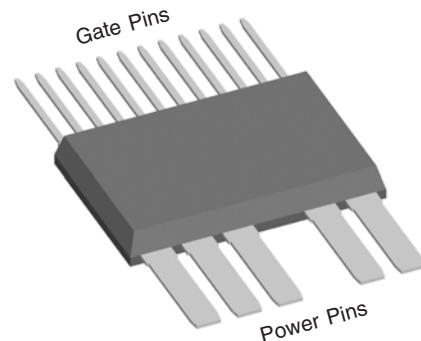
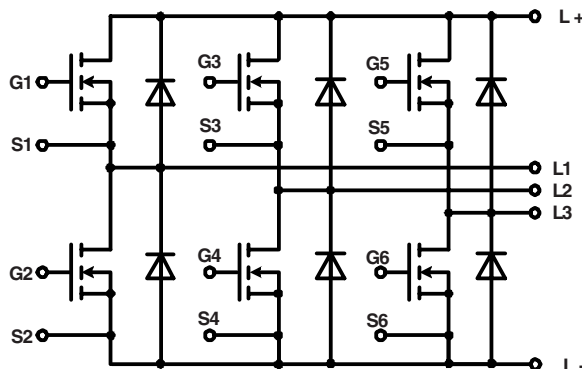
## Three phase full bridge

with Trench MOSFETs  
in DCB isolated high current package

$$V_{DSS} = 100 \text{ V}$$

$$I_{D25} = 70 \text{ A}$$

$$R_{DSon \text{ typ.}} = 11 \text{ m}\Omega$$



### MOSFETs

Symbol	Conditions	Maximum Ratings	
$V_{DSS}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	100	V
$V_{GS}$		$\pm 20$	V
$I_{D25}$	$T_C = 25^{\circ}\text{C}$	70	A
$I_{D90}$	$T_C = 90^{\circ}\text{C}$	50	A
$I_{F25}$	$T_C = 25^{\circ}\text{C}$ (diode)	130	A
$I_{F90}$	$T_C = 90^{\circ}\text{C}$ (diode)	85	A

### Applications

- AC drives
- in automobiles
    - electric power steering
    - starter generator
  - in industrial vehicles
    - propulsion drives
    - fork lift drives
  - in battery supplied equipment

### Features

- MOSFETs in trench technology:
  - low  $R_{DSon}$
  - optimized intrinsic reverse diode
- package:
  - high level of integration
  - high current capability
  - auxiliary terminals for MOSFET control
  - terminals for soldering or welding connections
  - isolated DCB ceramic base plate with optimized heat transfer

Symbol	Conditions	Characteristic Values		
		$(T_{VJ} = 25^{\circ}\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
$R_{DSon}$	on chip level at $\left. \begin{array}{l} T_{VJ} = 25^{\circ}\text{C} \\ V_{GS} = 10 \text{ V}; I_D = 35 \text{ A} \end{array} \right\} T_{VJ} = 125^{\circ}\text{C}$		11	14
			24	mΩ
$V_{GSth}$	$V_{DS} = 20 \text{ V}; I_D = 1 \text{ mA}$	2		4
				V
$I_{DSS}$	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	1
				$\mu\text{A}$
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2
				$\mu\text{A}$
$Q_g$	$\left. \begin{array}{l} V_{GS} = 10 \text{ V}; V_{DS} = 80 \text{ V}; I_D = 25 \text{ A} \end{array} \right\}$		110	nC
$Q_{gs}$			18	nC
$Q_{gd}$			44	nC
$t_{d(on)}$	$\left. \begin{array}{l} V_{GS} = 10 \text{ V}; V_{DS} = 30 \text{ V}; \\ I_D = 25 \text{ A}; R_G = 10 \Omega \end{array} \right\}$		35	ns
$t_r$			85	ns
$t_{d(off)}$			150	ns
$t_f$			70	ns
$V_F$	(diode) $I_F = 35 \text{ A}; V_{GS} = 0 \text{ V}$		0.8	1.25
				V
$t_{rr}$	(diode) $I_F = 75 \text{ A}; -di/dt = 100 \text{ A}/\mu\text{s}; V_{DS} = 30 \text{ V}$		80	ns
$R_{thJC}$	with heat transfer paste			0.85
$R_{thJH}$			1.7	K/W
				K/W

IXYS reserves the right to change limits, test conditions and dimensions.

